

DUAL P-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

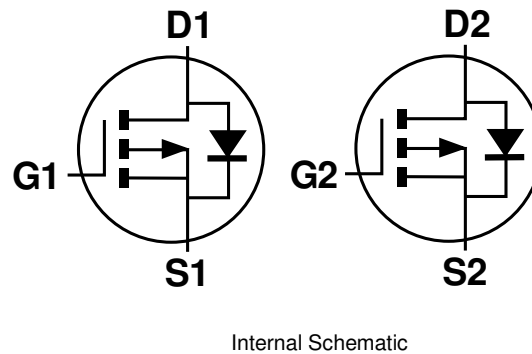
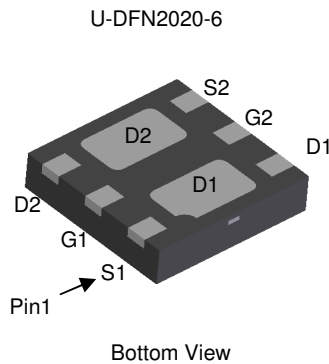
Device	$V_{(BR)DSS}$	$R_{DS(ON) max}$	$I_D MAX$ $T_A = +25^\circ C$
P-Channel	-12V	61m Ω @ $V_{GS} = -4.5V$	-3.8A
		81m Ω @ $V_{GS} = -2.5V$	-3.3A
		115m Ω @ $V_{GS} = -1.8V$	-2.8A

Description

This MOSFET is designed to minimize the on-state resistance ($R_{DS(on)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

Applications

- Load Switch
- Power Management Functions
- Portable Power Adaptors



Features

- Low On-Resistance
- Low Input Capacitance
- Low Profile, 0.6mm Max Height
- **Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

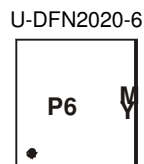
- Case: U-DFN2020-6
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish NiPdAu over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @4
- Terminals Connections: See Diagram Below
- Weight: 0.0065 grams (Approximate)

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP1046UFDB -7	U-DFN2020-6	3,000/Tape & Reel
DMP1046UFDB -13	U-DFN2020-6	10,000/Tape & Reel

- Notes:
1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.
 2. See <http://www.diodes.com> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. For packaging details, go to our website at <http://www.diodes.com>.

Marking Information



P6 = Product Type Marking Code
 YM = Date Code Marking
 Y = Year (ex: C = 2015)
 M = Month (ex: 9 = September)

Date Code Key

Year	2015	2016	2017	2018	2019	2020	2021
Code	C	D	E	F	G	H	I

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V _{DSS}	-12	V
Gate-Source Voltage			V _{GSS}	±8	V
Continuous Drain Current (Note 5) V _{GS} = 4.5V	Steady State	T _A = +25°C T _A = +70°C	I _D	-3.8 -3.0	A
	t < 5s	T _A = +25°C T _A = +70°C	I _D	-5.0 -4.0	A
Maximum Continuous Body Diode Forward Current (Note 5)			I _S	-1	A
Pulsed Drain Current (10μs pulse, duty cycle = 1%)			I _{DM}	-15	A
Avalanche Current (L = 0.1mH)			I _{AS}	-12	A
Avalanche Energy (L = 0.1mH)			E _{AS}	8	mJ

Thermal Characteristics

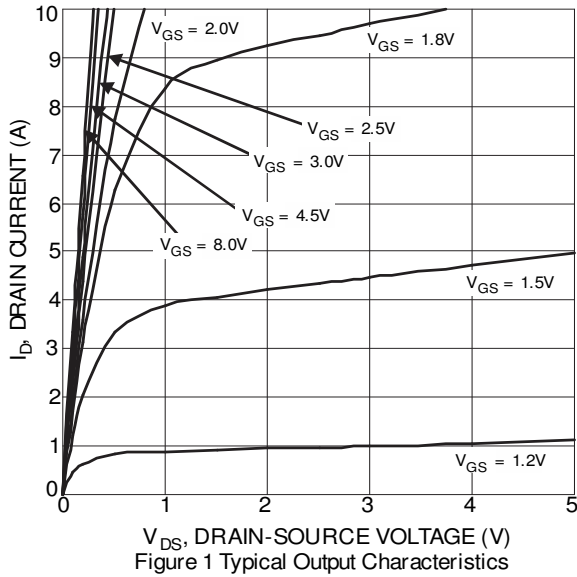
Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)	Steady State	P _D	1.4	W
	t < 5s		2.2	
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	R _{θJA}	92	°C/W
	t < 5s		55	
Thermal Resistance, Junction to Case (Note 5)		R _{θJC}	20	
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to 150	°C

Notes: 5. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.

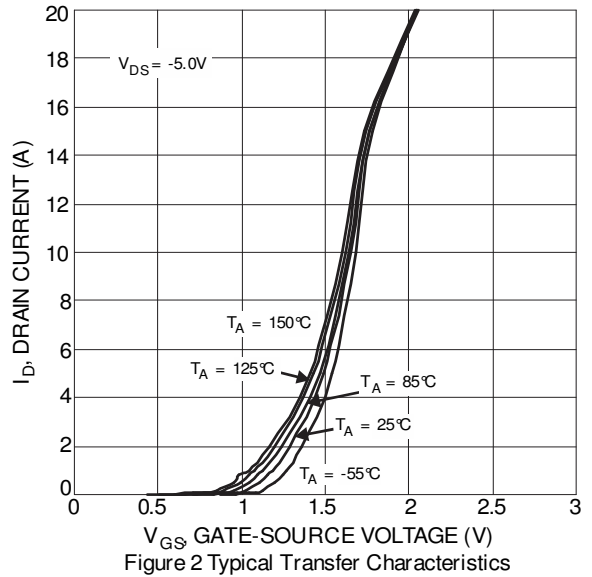
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 6)						
Drain-Source Breakdown Voltage	BV _{DSS}	-12	-	-	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	-	-	-1.0	μA	V _{DS} = -12V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	-	-	±100	nA	V _{GS} = ±8V, V _{DS} = 0V
ON CHARACTERISTICS (Note 6)						
Gate Threshold Voltage	V _{GS(th)}	-0.4	-	-1	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(on)}	-	37	61	mΩ	V _{GS} = -4.5V, I _D = -3.6A
		-	47	81		V _{GS} = -2.5V, I _D = -3.2A
		-	63	115		V _{GS} = -1.8V, I _D = -1.0A
Diode Forward Voltage	V _{SD}	-	-0.65	-1.2	V	V _{GS} = 0V, I _S = -4.5A
DYNAMIC CHARACTERISTICS (Note 7)						
Input Capacitance	C _{iss}	-	915	-	pF	V _{DS} = -6V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	-	225	-	pF	
Reverse Transfer Capacitance	C _{rss}	-	183	-	pF	
Gate Resistance	R _g	-	56.9	-	Ω	V _{DS} = 0V, V _{GS} = 0V, f = 1MHz
Total Gate Charge (V _{GS} = -4.5V)	Q _g	-	10.7	-	nC	V _{DS} = -6V, I _D = -4.3A
Total Gate Charge (V _{GS} = -8V)		-	17.9	-	nC	
Gate-Source Charge	Q _{gs}	-	1.7	-	nC	
Gate-Drain Charge	Q _{gd}	-	3.0	-	nC	
Turn-On Delay Time	t _{D(on)}	-	5.7	-	ns	
Turn-On Rise Time	t _r	-	11.5	-	ns	V _{DD} = -6V, V _{GS} = -4.5V, R _L = 1.6Ω, R _G = 1Ω
Turn-Off Delay Time	t _{D(off)}	-	27.8	-	ns	
Turn-Off Fall Time	t _f	-	26.4	-	ns	

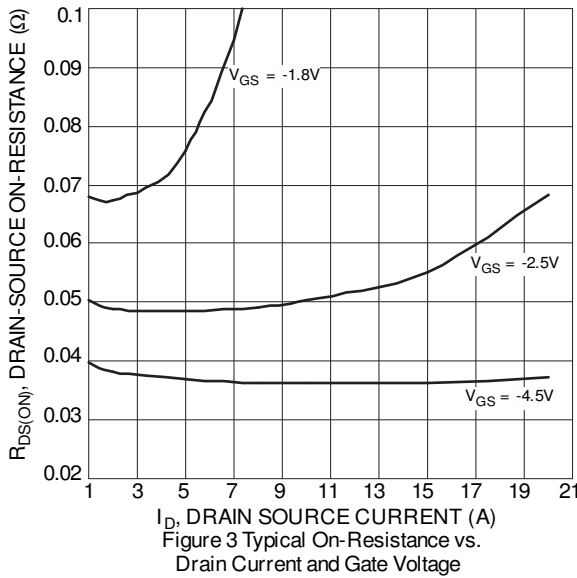
Notes: 6. Short duration pulse test used to minimize self-heating effect.
7. Guaranteed by design. Not subject to product testing.



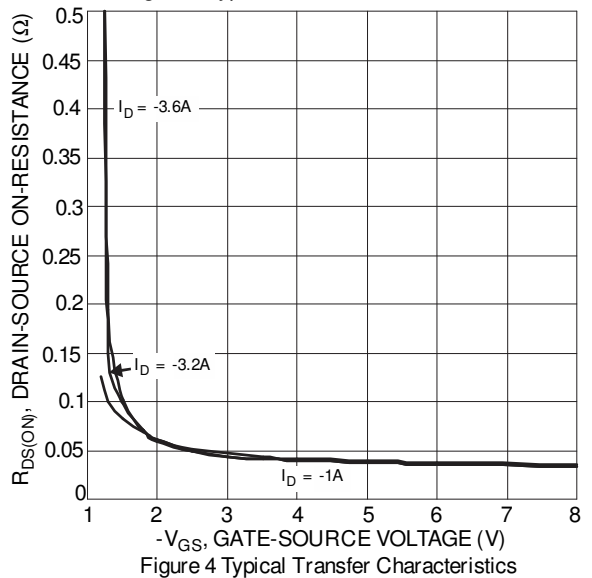
V_{DS} , DRAIN-SOURCE VOLTAGE (V)
Figure 1 Typical Output Characteristics



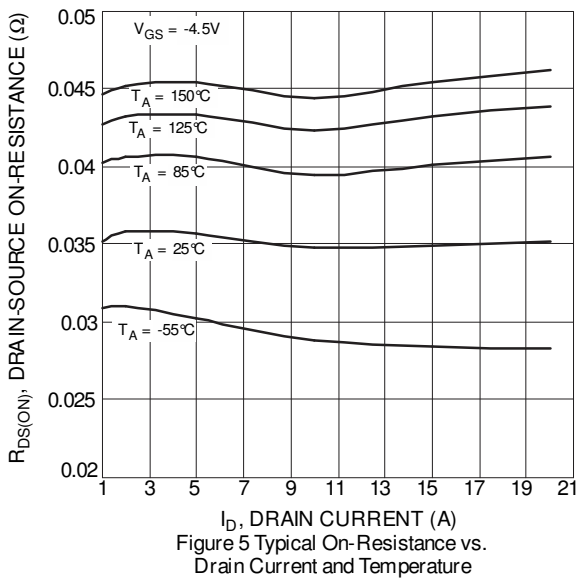
V_{GS} , GATE-SOURCE VOLTAGE (V)
Figure 2 Typical Transfer Characteristics



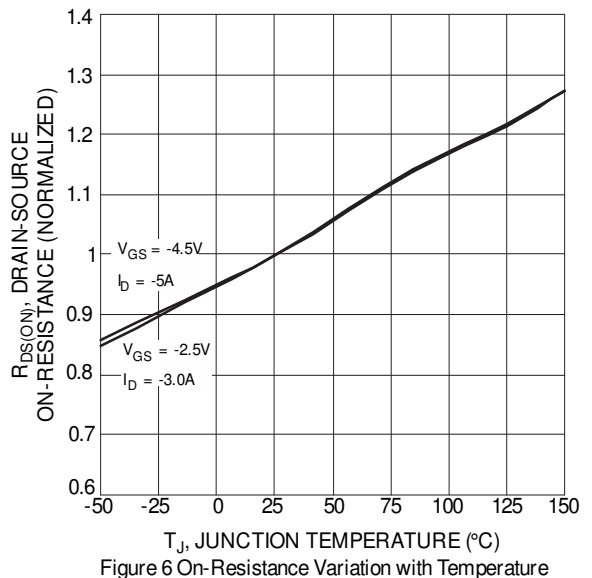
I_D , DRAIN SOURCE CURRENT (A)
Figure 3 Typical On-Resistance vs. Drain Current and Gate Voltage



$-V_{GS}$, GATE-SOURCE VOLTAGE (V)
Figure 4 Typical Transfer Characteristics



I_D , DRAIN CURRENT (A)
Figure 5 Typical On-Resistance vs. Drain Current and Temperature



T_J , JUNCTION TEMPERATURE ($^{\circ}C$)
Figure 6 On-Resistance Variation with Temperature

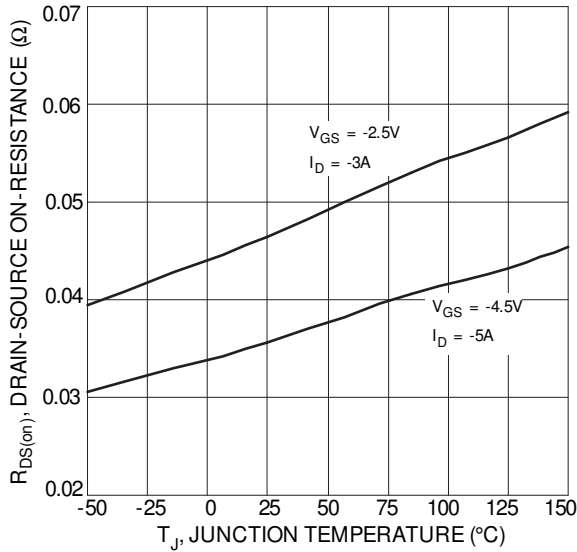


Figure 7 On-Resistance Variation with Temperature

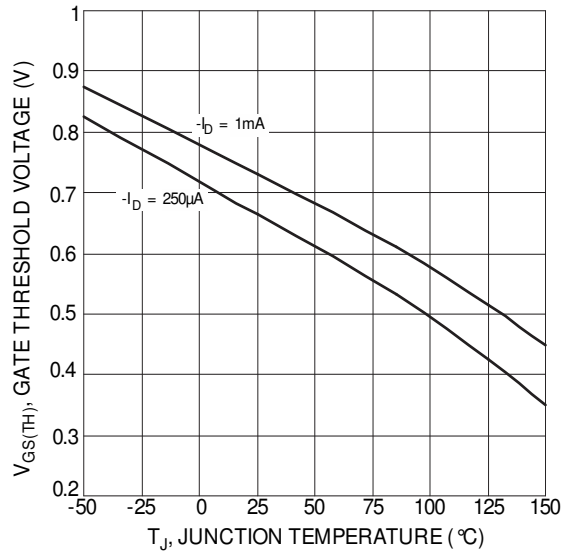


Figure 8 Gate Threshold Variation vs. Ambient Temperature

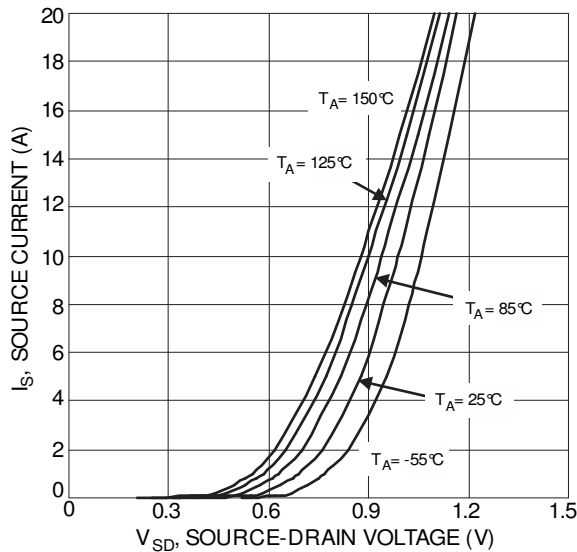


Figure 9 Diode Forward Voltage vs. Current

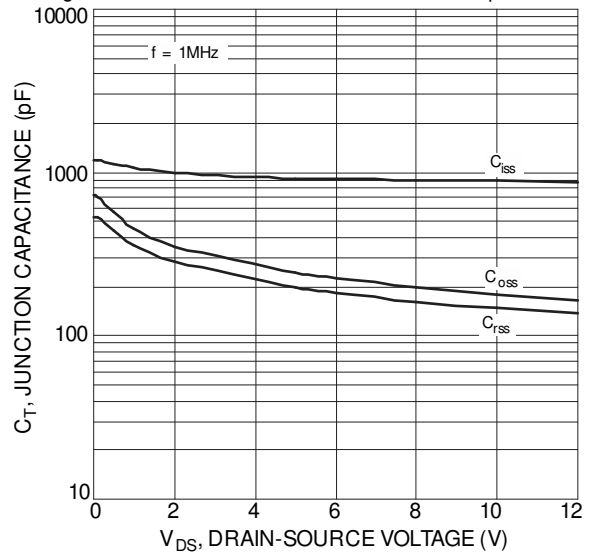


Figure 10 Typical Junction Capacitance

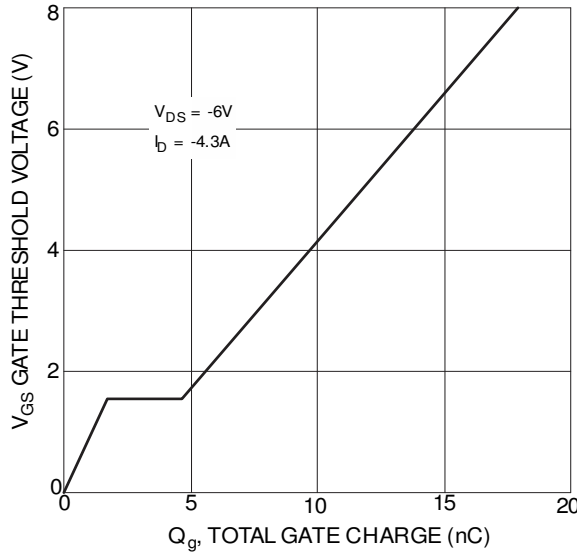


Figure 11 Gate Charge

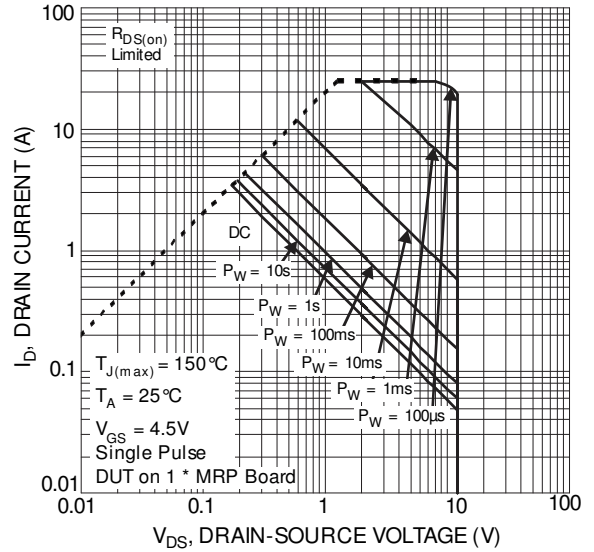


Figure 12 SOA, Safe Operation Area

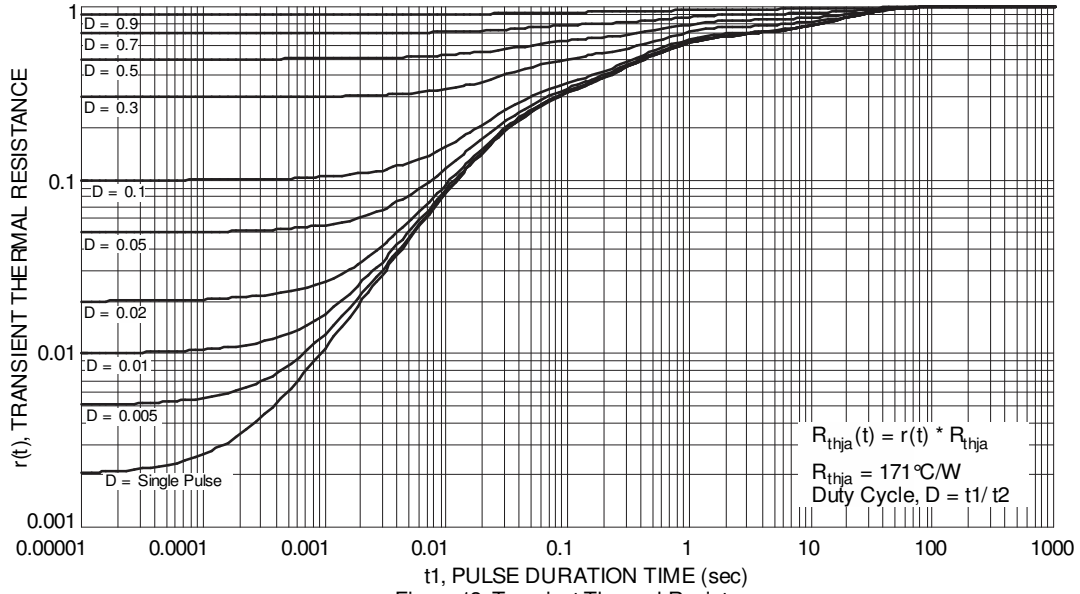
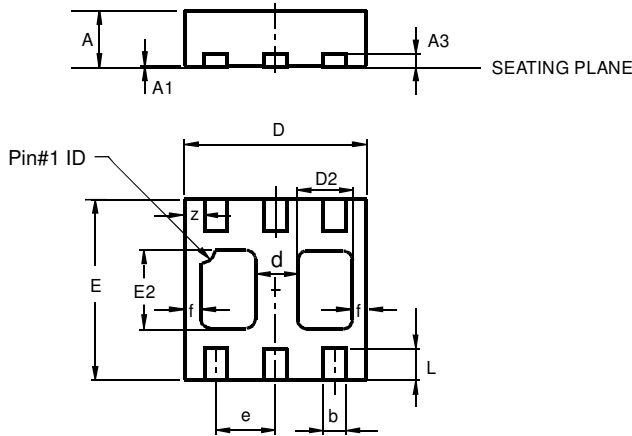


Figure 13 Transient Thermal Resistance

Package Outline Dimensions

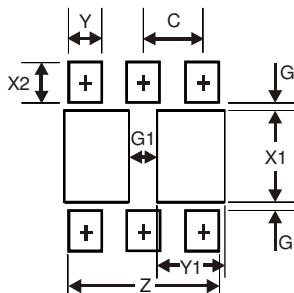
Please see AP02002 at <http://www.diodes.com/datasheets/ap02002.pdf> for the latest version.



U-DFN2020-6 Type B			
Dim	Min	Max	Typ
A	0.545	0.605	0.575
A1	0	0.05	0.02
A3	—	—	0.13
b	0.20	0.30	0.25
D	1.95	2.075	2.00
d	—	—	0.45
D2	0.50	0.70	0.60
e	—	—	0.65
E	1.95	2.075	2.00
E2	0.90	1.10	1.00
f	—	—	0.15
L	0.25	0.35	0.30
z	—	—	0.225
All Dimensions in mm			

Suggested Pad Layout

Please see AP02001 at <http://www.diodes.com/datasheets/ap02001.pdf> for the latest version.



Dimensions	Value (in mm)
Z	1.67
G	0.20
G1	0.40
X1	1.0
X2	0.45
Y	0.37
Y1	0.70
C	0.65

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